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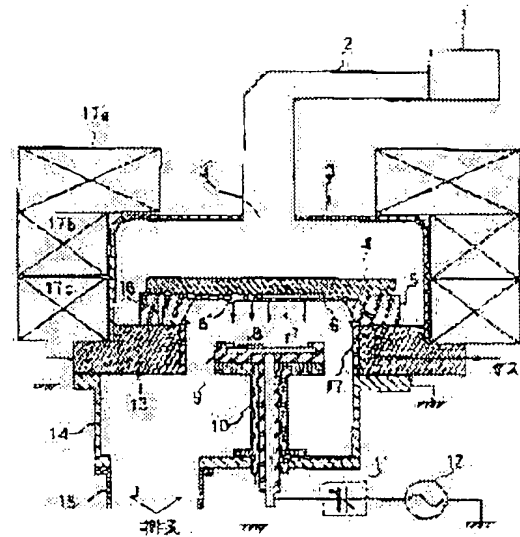
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(54) PLASMA TREATMENT DEVICE

(57)Abstract:

PURPOSE: To enhance productivity of a plasma treatment device by a method wherein a uniform μ -wave plasma is produced, and on a substrate as a work, high frequency bias is set uniform.

CONSTITUTION: A counter electrode 4 is provided making its surface exposed to a vacuum and larger in area than the processing plane of a substrate 7 as a work to confront the substrate 7, and μ waves are guided into a vacuum through the intermediary of a quartz ring 5 provided to the lower periphery of the counter electrode 4. A grounding potential and a high frequency power supply are applied to the substrate 7 and the counter electrode 4 respectively, whereby optimal processing conditions can be obtained. By this setup, not only a uniform plasma can be obtained but also a bias potential can be set uniform throughout the substrate 7 through this invention, so that a plasma treatment device of this design can be enhanced in productivity.



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